

AMENDMENTS TO THE CLAIMS

This listing of claims replaces all prior versions, and listings, of claims in the application.

1. (Currently Amended) A semiconductor integrated circuit device comprising:
a resonant circuit resonating at an arbitrary frequency;
a transmission line for transmitting a high-frequency signal having ~~said~~ the frequency,
wherein a first end of said transmission line ~~being~~ is connected to said resonant circuit;
an active element having a first electrode connected to a second end of said
transmission line, a second electrode which is grounded through a reactance element, and a
third electrode;
an output-matching circuit including a diode section for regulating an oscillation
power and a high-frequency signal output terminal, wherein a first end of said diode section
is connected to said third electrode of said active element, and said high-frequency signal
output terminal is connected to a second end of said diode section; and
a substrate having a main surface on which said resonant circuit, said transmission
line, said active element, and said output-matching circuit are arranged.
2. (Currently Amended) The semiconductor integrated circuit device according to
claim 1, wherein said diode section includes a plurality of diodes ~~having~~ connected in an
inverse parallel arrangement.
3. (Currently Amended) The semiconductor integrated circuit device according to
claim 1, wherein said diode section includes a plurality of diodes ~~arranged~~ connected in
series.
4. (Original) The semiconductor integrated circuit device according to claim 1,
further comprising a bias circuit for applying a DC bias to said diode section.
5. (Currently Amended) A semiconductor integrated circuit device comprising:
a resonant circuit resonating at an arbitrary frequency;

a transmission line for transmitting a high-frequency signal having ~~said~~ the frequency, wherein a first end of said transmission line ~~being~~ is connected to said resonant circuit;

an oscillation power regulating circuit including a diode section for regulating ~~an~~ oscillation power, wherein said oscillation power regulating circuit is connected to a second end of said transmission line;

an active element having a first electrode connected to the second end of said transmission line, a second electrode which is grounded through a reactance element, and a third electrode;

an output-matching circuit including a high-frequency signal output terminal, wherein said output-matching circuit is connected to said third electrode of said active element; and

a substrate having a main surface on which said resonant circuit, said transmission line, said oscillation power regulating circuit, said active element, and said output-matching circuit are arranged.

6. (Currently Amended) The semiconductor integrated circuit device according to claim 5, wherein said diode section includes a plurality of diodes ~~having~~ connected in an inverse parallel arrangement.

7. (Currently Amended) The semiconductor integrated circuit device according to claim 5, wherein said diode section includes a plurality of diodes ~~arranged~~ connected in series.

8. (Original) The semiconductor integrated circuit device according to claim 5, further comprising a bias circuit for applying a DC bias to said diode section.